



## DESCRIPTION

AM2319 is available in a SOT-23S package.

## ORDERING INFORMATION

Package Type	Part Number	
SOT-23S	E3S	AM2319E3SR
		AM2319E3SVR
Note	V: Halogen free Package R: Tape & Reel	
AiT provides all RoHS products Suffix " V " means Halogen free Package		

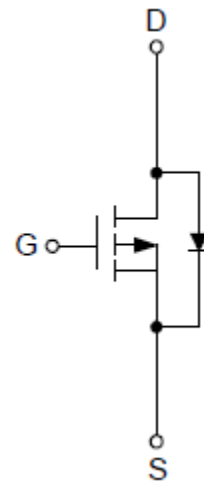
## FEATURES

- -40V/-3A,  
 $R_{DS(ON)} = 80m\Omega(\text{max.}) @ V_{GS} = -10V$   
 $R_{DS(ON)} = 120m\Omega(\text{max.}) @ V_{GS} = -4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- Available in a SOT-23S package.

## APPLICATION

- Load Switch.
- DC/DC Converter.

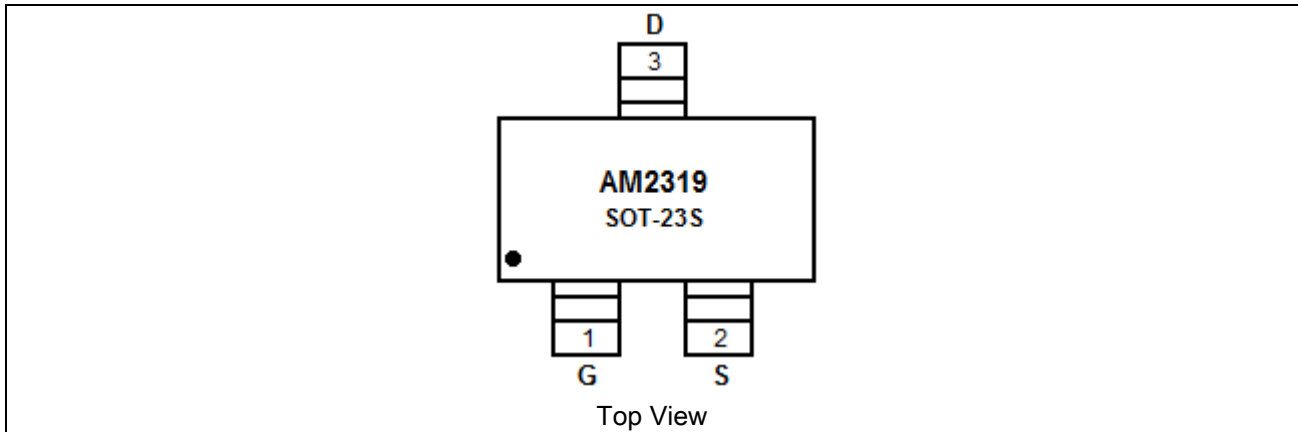
## PIN DESCRIPTION



P-Channel MOSFET



## PIN DESCRIPTION



Pin #	Symbol	Function
1	G	Gate
2	S	Source
3	D	Drain



## ABSOLUTE MAXIMUM RATINGS

T<sub>A</sub> = 25°C, unless otherwise noted

V <sub>DSS</sub> , Drain-Source Voltage		-40V
V <sub>GSS</sub> , Gate-Source Voltage		±20V
T <sub>J</sub> , Maximum Junction Temperature		150°C
T <sub>STG</sub> , Storage Temperature Range		-55°C~150°C
I <sub>S</sub> , Diode Continuous Forward Current		-1A
I <sub>DM</sub> <sup>NOTE1</sup> , Pulsed Drain Current	T <sub>C</sub> =25°C	-12A
	T <sub>C</sub> =100°C	-7.6A
I <sub>D</sub> , Continuous Drain Current	T <sub>C</sub> =25°C	-3A
	T <sub>C</sub> =100°C	-1.9A
P <sub>D</sub> , Maximum Power Dissipation	T <sub>C</sub> =25°C	1.1W
	T <sub>C</sub> =100°C	0.4W
R <sub>θJA</sub> <sup>NOTE1</sup> , Thermal Resistance-Junction to Ambient	t ≤ 10sec.	115°C/W
	Steady state	160°C/W

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

NOTE1: Surface Mounted on 1in<sup>2</sup> pad area, t ≤ 10sec.



## ELECTRICAL CHARACTERISTICS

T<sub>A</sub> = 25°C, unless otherwise noted

Parameter	Symbol	Conditions	Min	Typ.	Max	Units
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250μA	-40	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V	-	-	-1	μA
		T <sub>J</sub> =85°C			-30	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250μA	-1.3	-1.9	-2.5	V
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Drain-Source On-state Resistance	R <sub>DS(ON)</sub> NOTE2	V <sub>GS</sub> =-10V, I <sub>DS</sub> =-3A	-	64	80	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.9A	-	90	120	
<b>Diode Characteristics</b>						
Diode Forward Voltage	V <sub>SD</sub> NOTE2	I <sub>SD</sub> =-1A, V <sub>GS</sub> =0V	-	-0.8	-1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>SD</sub> =-3A, dI <sub>SD</sub> /dt=100A/μs	-	18	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>		-	11	-	nC
<b>Dynamic Characteristics</b> NOTE3						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-20V, Frequency=1.0MHz	-	360	-	pF
Output Capacitance	C <sub>OSS</sub>		-	58	-	
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	40	-	
Turn-on Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> =-20V, R <sub>L</sub> =20Ω I <sub>DS</sub> =-1A, V <sub>GEN</sub> =-10V, R <sub>G</sub> =6Ω	-	8	-	ns
Turn-on Rise Time	t <sub>r</sub>		-	6	-	
Turn-off Delay Time	t <sub>D(OFF)</sub>		-	25	-	
Turn-off Fall Time	t <sub>f</sub>		-	14	-	
<b>Gate Charge Characteristics</b> NOTE3						
Total Gate Charge	Q <sub>G</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-10V, I <sub>DS</sub> =-3A	-	8.3	-	nC
Gate-Source Charge	Q <sub>GS</sub>		-	1.7	-	
Gate-Drain Charge	Q <sub>GD</sub>		-	1.9	-	

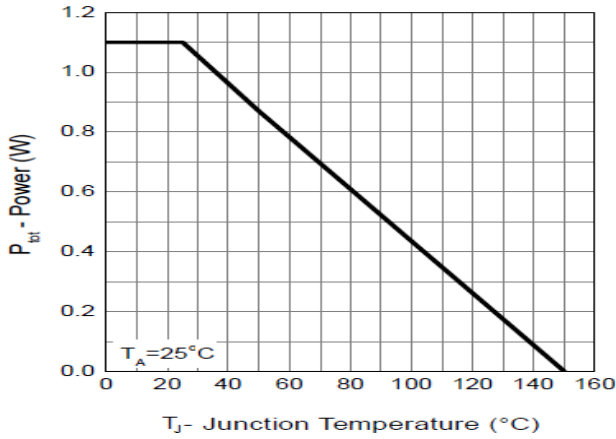
NOTE2: Pulse test; pulse width≤300μs, duty cycle≤2%.

NOTE3: Guaranteed by design, not subject to production testing.

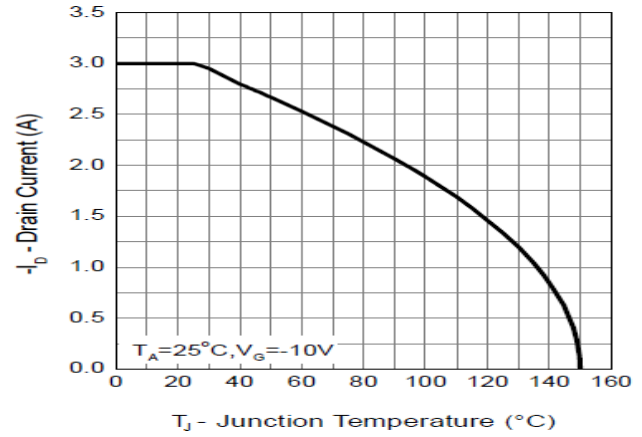


**TYPICAL CHARACTERISTICS**

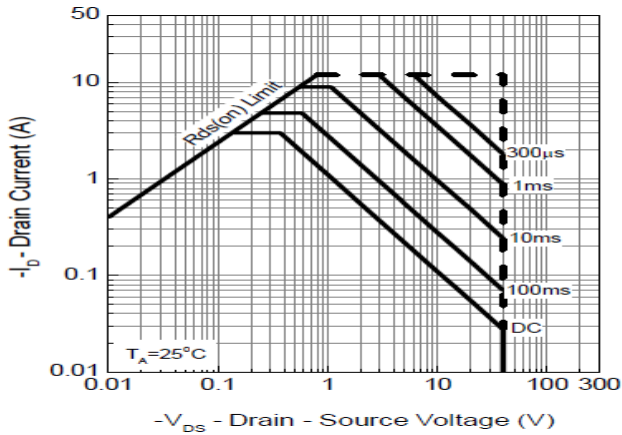
1. Power Dissipation



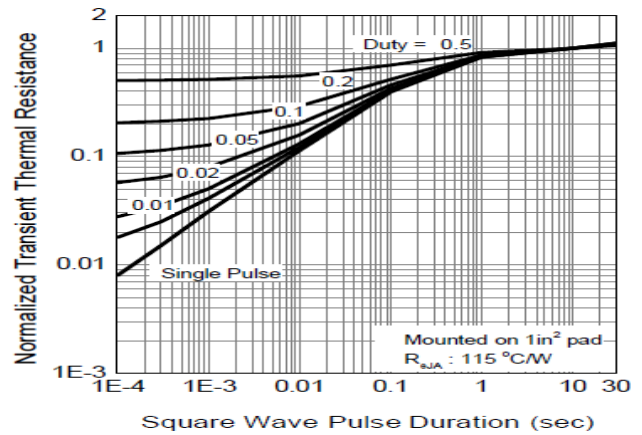
2. Drain Current



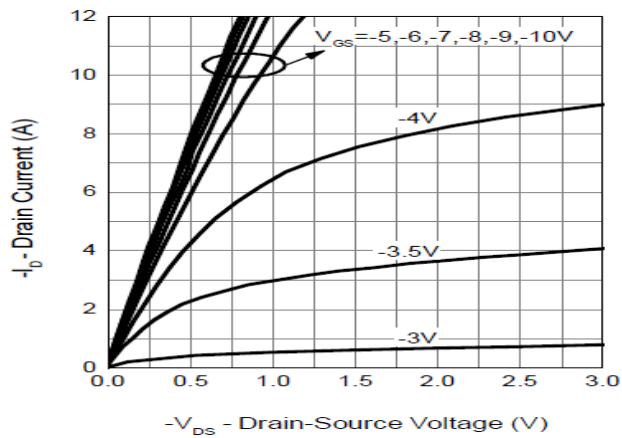
3. Safe Operation Area



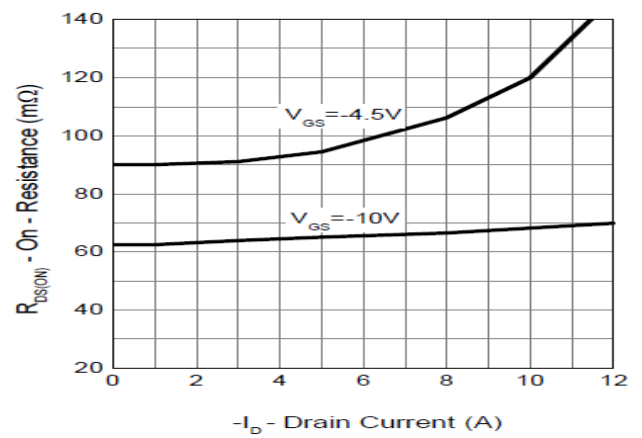
4. Thermal Transient Impedance



5. Output Characteristics

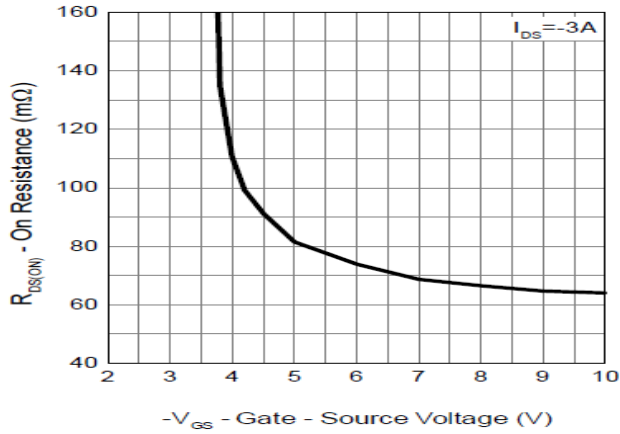


6. Drain-Source On Resistance

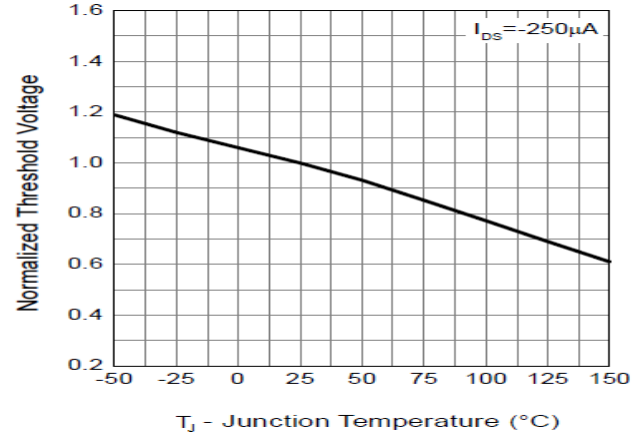




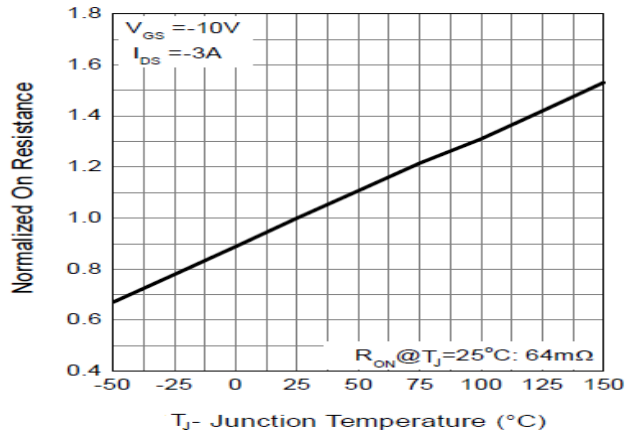
7. Gate-Source On Resistance



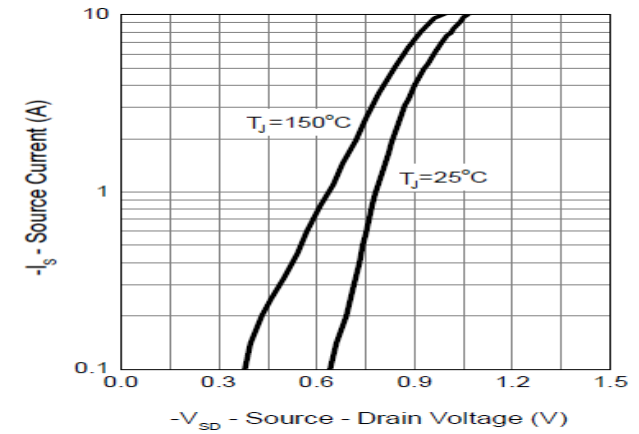
8. Gate Threshold Voltage



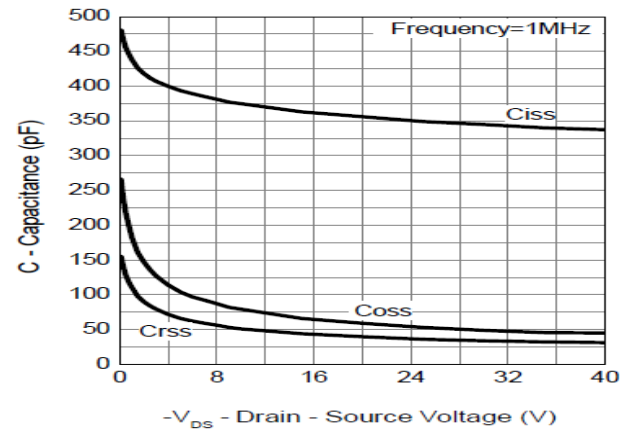
9. Drain-Source On Resistance



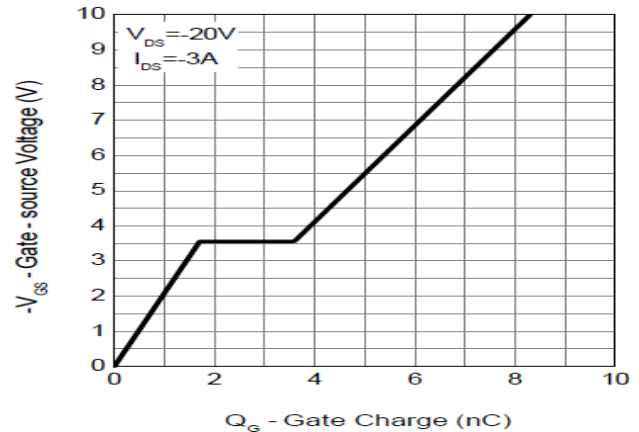
10. Source-Drain Diode Forward



11. Capacitance



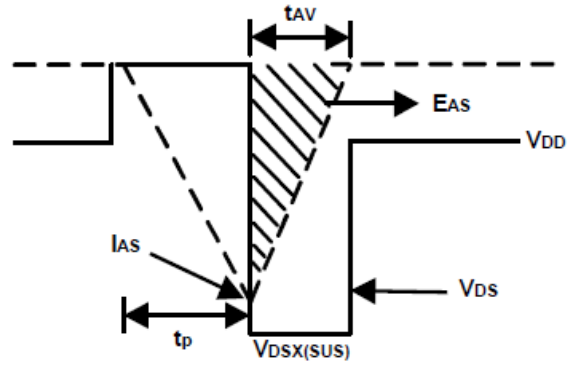
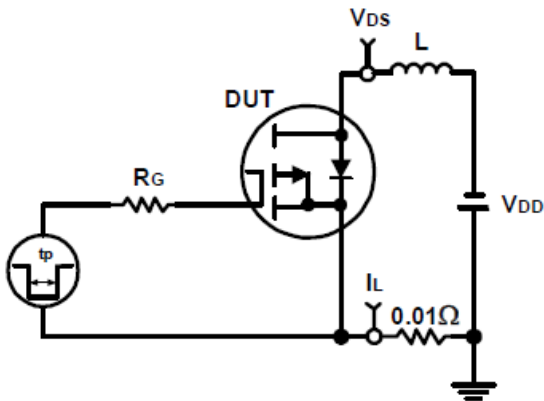
12. Gate Charge



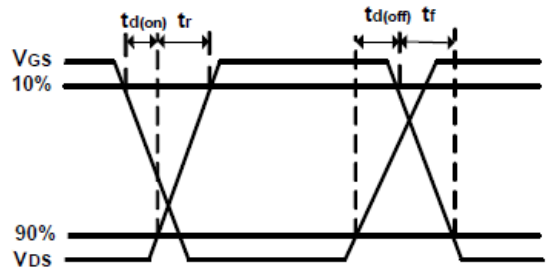
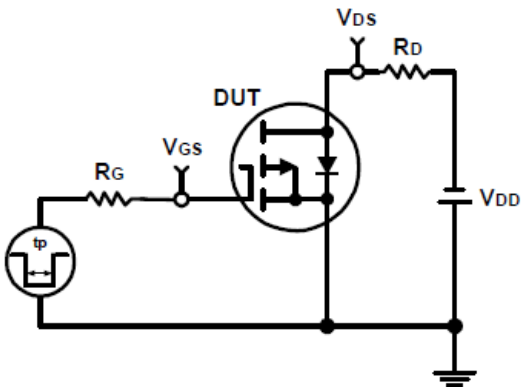


## DETAILED INFORMATION

### Avalanche Test Circuit and Waveforms



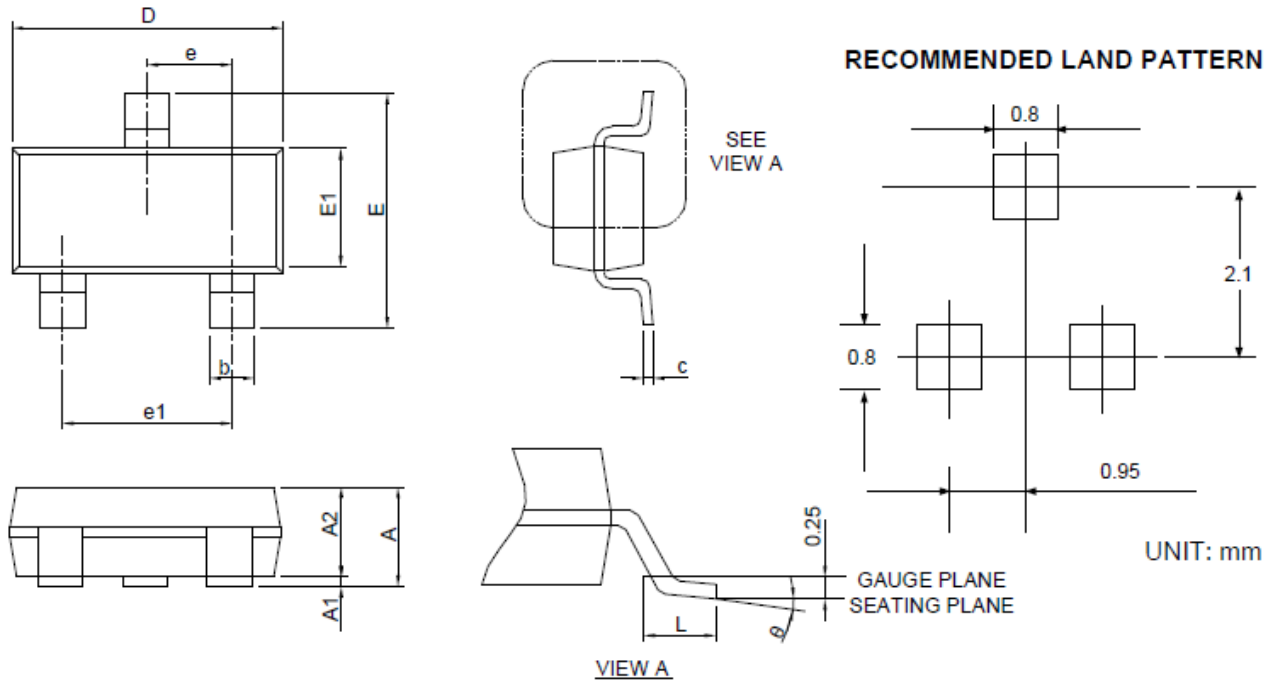
### Switching Time Test Circuit and Waveforms





**PACKAGE INFORMATION**

Dimension in SOT-23S Package (Unit: mm)



SYMBOL	MIN	MAX
A	-	1.200
A1	0.000	0.150
A2	0.900	1.300
b	0.300	0.500
c	0.080	0.220
D	2.700	3.100
E	2.200	2.600
E1	1.200	1.400
e	0.950(BSC)	
e1	1.900(BSC)	
L	0.300	0.600
θ	0°	8°





## IMPORTANT NOTICE

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